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TBLP  
11-25-02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of ) Art Unit: 2815  
Hongyong Zhang et al. ) Examiner: E. Lee  
Serial No. 09/190,618 )  
Filed: November 12, 1998 )  
For: SEMICONDUCTOR DEVICE AND )  
METHOD OF FABRICATING )  
THE SAME )

CERTIFICATE OF MAILING

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Washington, D.C. 20231, on 11-6-02

AMENDMENT

Honorable Commissioner of Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated August 6, 2002 please amend the above-  
identified application as follows:

IN THE SPECIFICATION:

Page 8, after the seventh full paragraph, please insert:

C1 --Fig. 9 is a diagram showing a device of the present invention illustrating a  
multilayered gate electrode in accordance with the present invention.--

Page 4, please amend the third full paragraph as follows:

C2 --Referring to Figs. 1A to 1E, a basic process for fabricating a TFT according to  
the present invention is described below. A base insulating film 102 is formed on a  
substrate 101. An active layer 103 is formed from a crystalline semiconductor (a  
semiconductor comprising a crystal even at a small quantity, for example, a single  
crystal semiconductor, polycrystalline semiconductor, semi-amorphous semiconductor  
or the like is referred to as "a crystalline semiconductor" in the present invention. An  
insulating film 104 comprising silicon oxide is formed to cover an active layer 103, and a  
coating is formed by an anodically oxidizable material. Preferably, an anodically

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